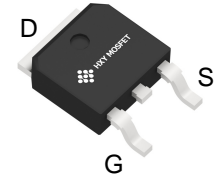




Description

The IRFR8314PBF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L

General Features

$V_{DS} = 30V$ $I_D = 160A$

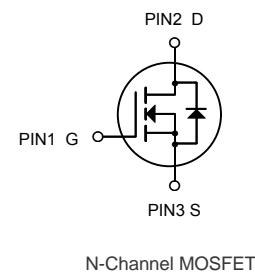
$R_{DS(ON)} < 2.3 m\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRFR8314PBF	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	160	A
$I_D @ T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
I_{DM}	Pulsed Drain Current ²	450	A
EAS	Single Pulse Avalanche Energy ³	580	mJ
I_{AS}	Avalanche Current	60	A
$P_D @ T_C=25^\circ C$	Total Power Dissipation ⁴	87	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient 1	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case1	2.1	$^\circ C/W$



Electrical characteristic ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain to source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	30			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	$I_D=250\mu A$, referenced to 25°C		0.02		V/ $^\circ\text{C}$
I_{DSS}	Drain to source leakage current	$V_{DS}=30V, V_{GS}=0V$			1	μA
		$V_{DS}=24V, T_J=125^\circ\text{C}$			50	μA
I_{GSS}	Gate to source leakage current, forward	$V_{GS}=20V, V_{DS}=0V$			100	nA
	Gate to source leakage current, reverse	$V_{GS}=-20V, V_{DS}=0V$			-100	nA
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2		2.4	V
$R_{DS(ON)}$	Drain to source on state resistance	$V_{GS}=4.5V, I_D=30A, T_J=25^\circ\text{C}$		2.2	4.8	m Ω
		$V_{GS}=10V, I_D=30A, T_J=25^\circ\text{C}$		1.6	2.3	m Ω
		$V_{GS}=10V, I_D=30A, T_J=125^\circ\text{C}$		2.5		m Ω
G_{fs}	Forward transconductance	$V_{DS}=5V, I_D=30A$		73		S
C_{iss}	Input capacitance			6272		pF
C_{oss}	Output capacitance	$V_{GS}=0V, V_{DS}=15V, f=1\text{MHz}$		1022		
C_{rss}	Reverse transfer capacitance			718		
$t_{d(on)}$	Turn on delay time			20		ns
t_r	Rising time	$V_{DS}=15V, I_D=30A, R_G=4.7\Omega, V_{GS}=10V$		58		
$t_{d(off)}$	Turn off delay time	(note 4,5)		158		
t_f	Fall time			77		
Q_g	Total gate charge	$V_{DS}=24V, V_{GS}=10V, I_D=30A, I_G=5\text{mA}$		143		nC
Q_{gs}	Gate-source charge	(note 4,5)		17		
Q_{gd}	Gate-drain charge			43		
R_g	Gate resistance	$V_{DS}=0V$, Scan F mode		4.2		Ω
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			110	A
I_{SM}	Pulsed source current				440	A
V_{SD}	Diode forward voltage drop.	$I_S=45A, V_{GS}=0V$			1.4	V
t_{rr}	Reverse recovery time	$I_S=30A, V_{GS}=0V,$		26		ns
Q_{rr}	Reverse recovery charge	$di_F/dt=100A/\mu s$		10		nC

※. Notes

1. Repeattive rating : pulse width limited by junction temperature.
2. $L=0.5\text{mH}, I_{AS}=48A, V_{DD}=30V, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
3. $I_{SD} \leq 30A, di/dt = 100A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.



Typical Characteristics

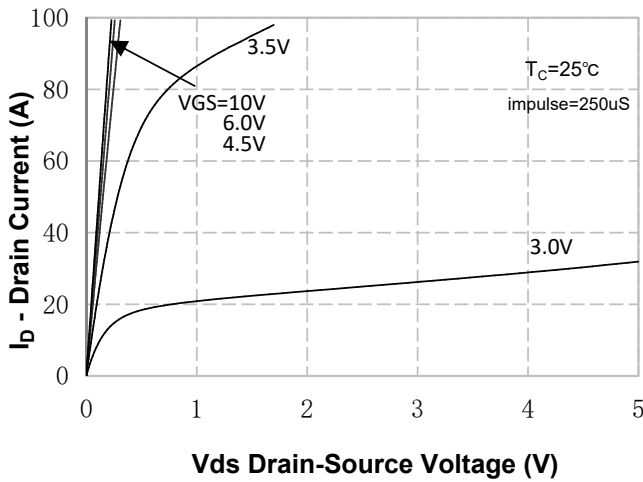


Figure 1. On-Region Characteristics

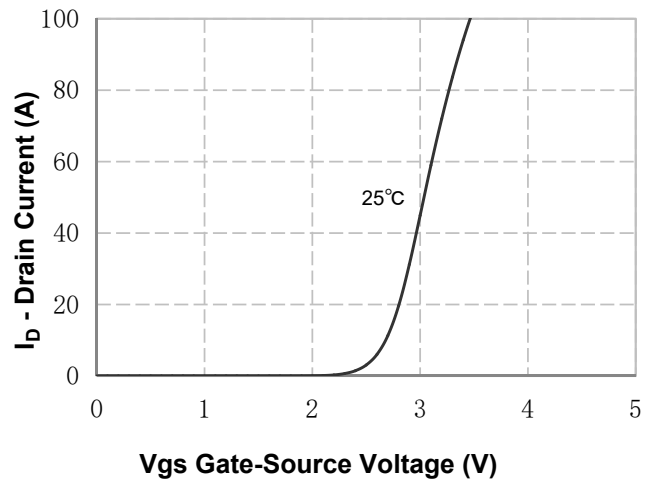


Figure 2. Transfer Characteristics

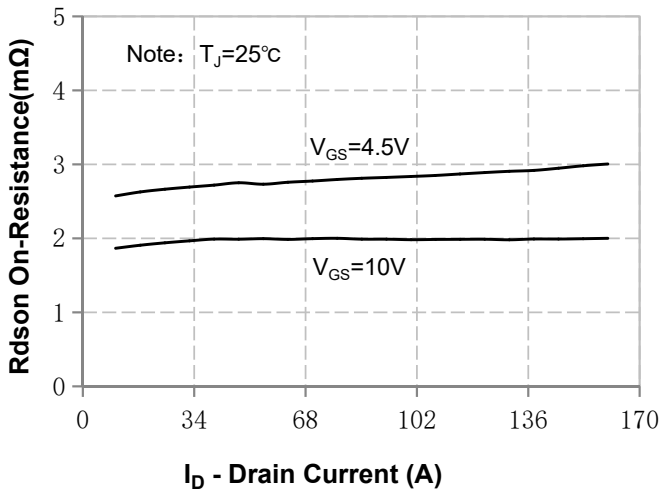


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

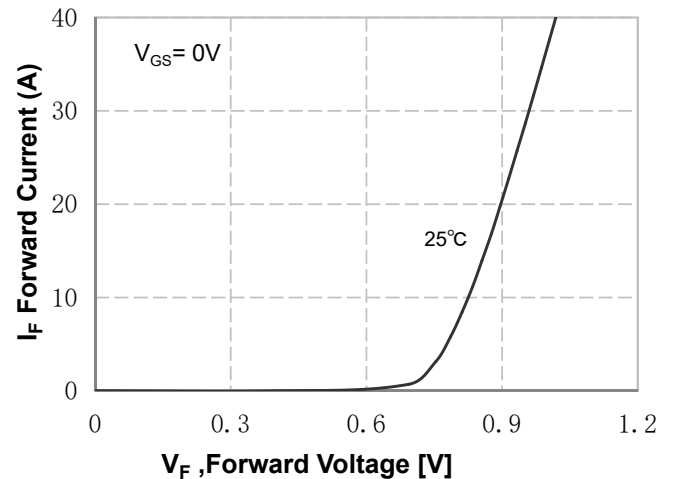


Figure 4. Body Diode Forward Voltage Variation vs Source Current

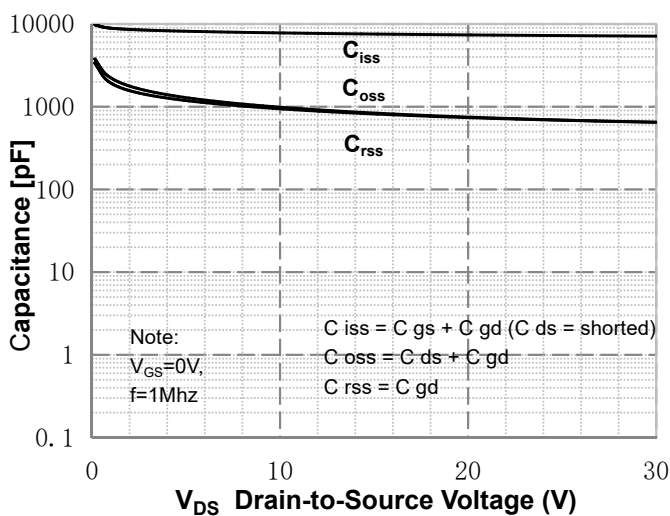


Figure 5. Capacitance Characteristics

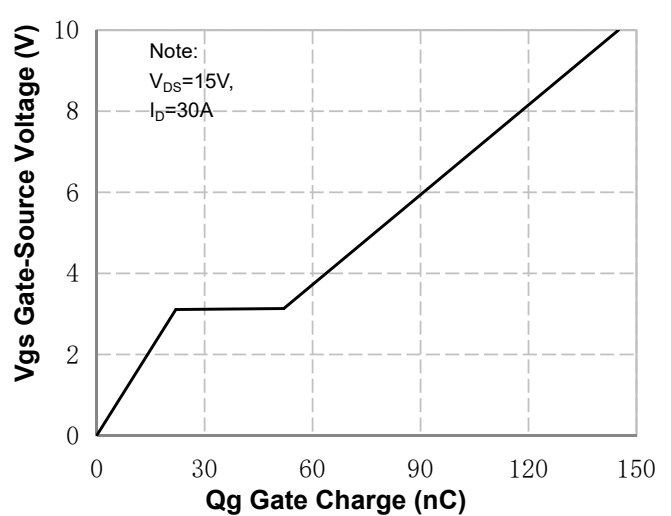


Figure 6. Gate Charge Characteristics

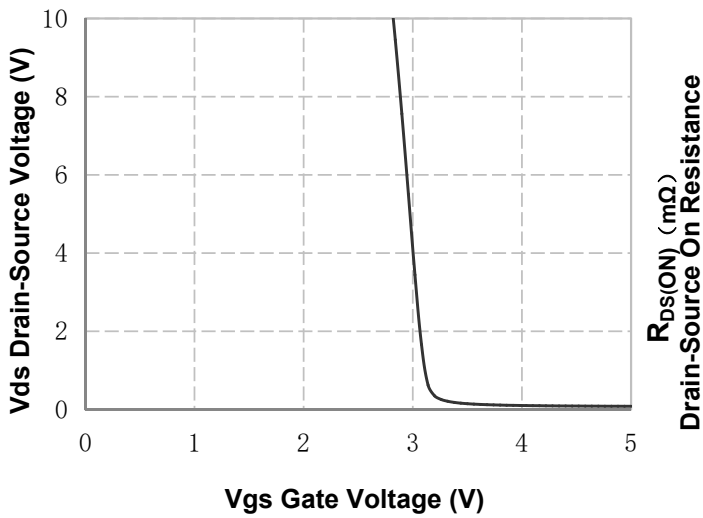


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

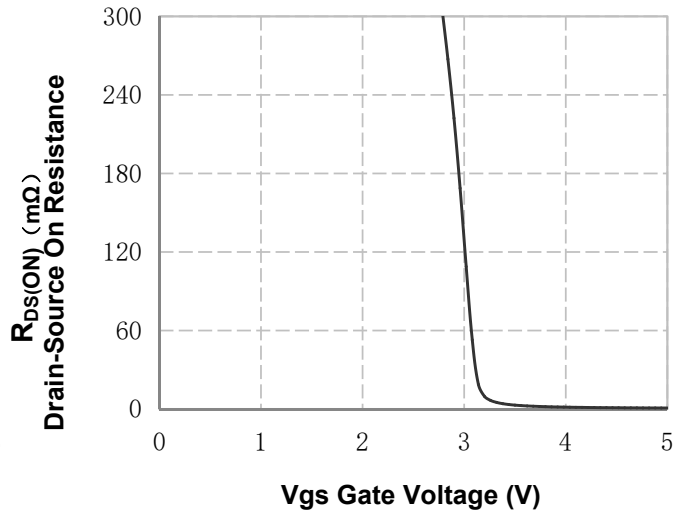


Figure 8. On-Resistance vs Gate Voltage

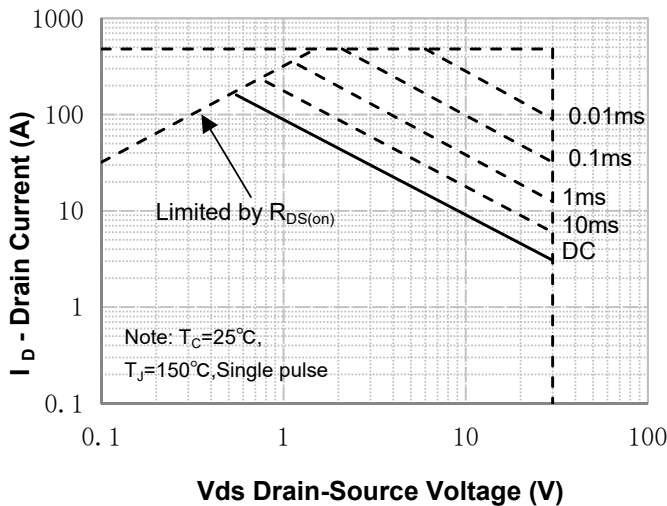


Figure 9. Maximum Safe Operating Area

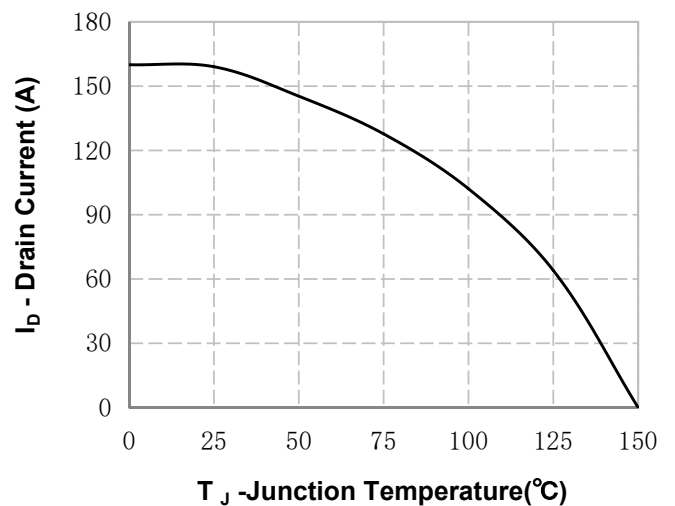


Figure 10. Maximum Continuous Drain Current vs Temperature

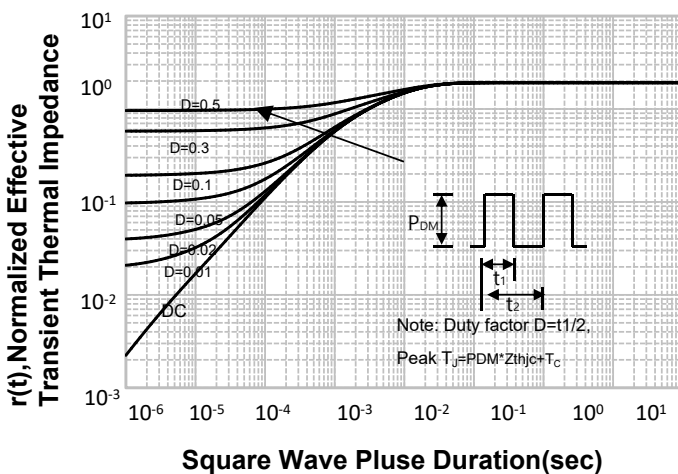
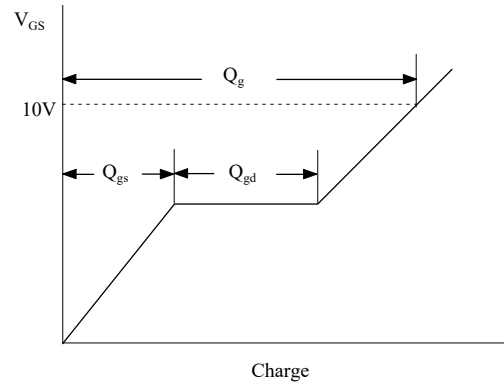
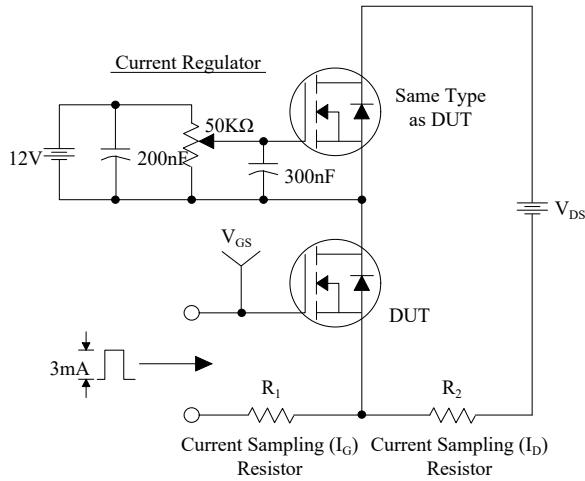


Figure 11. Transient Thermal Response Curve

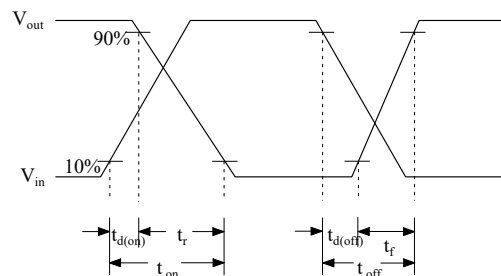
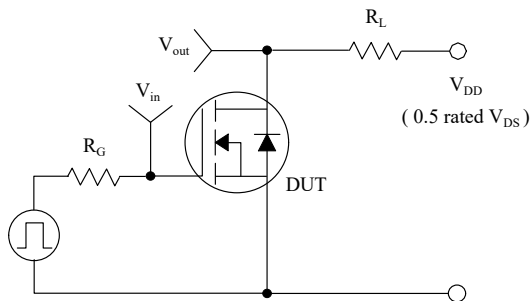


TestCircuit

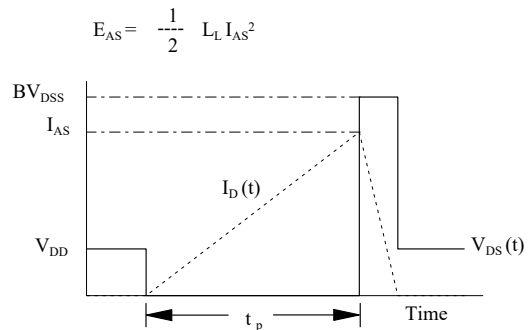
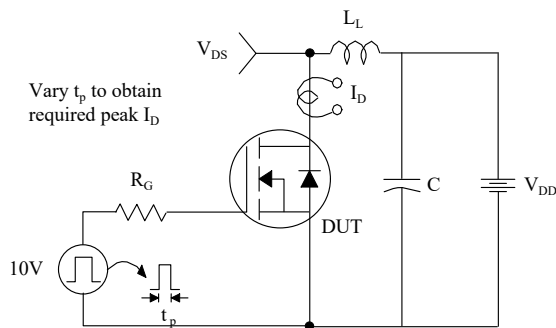
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

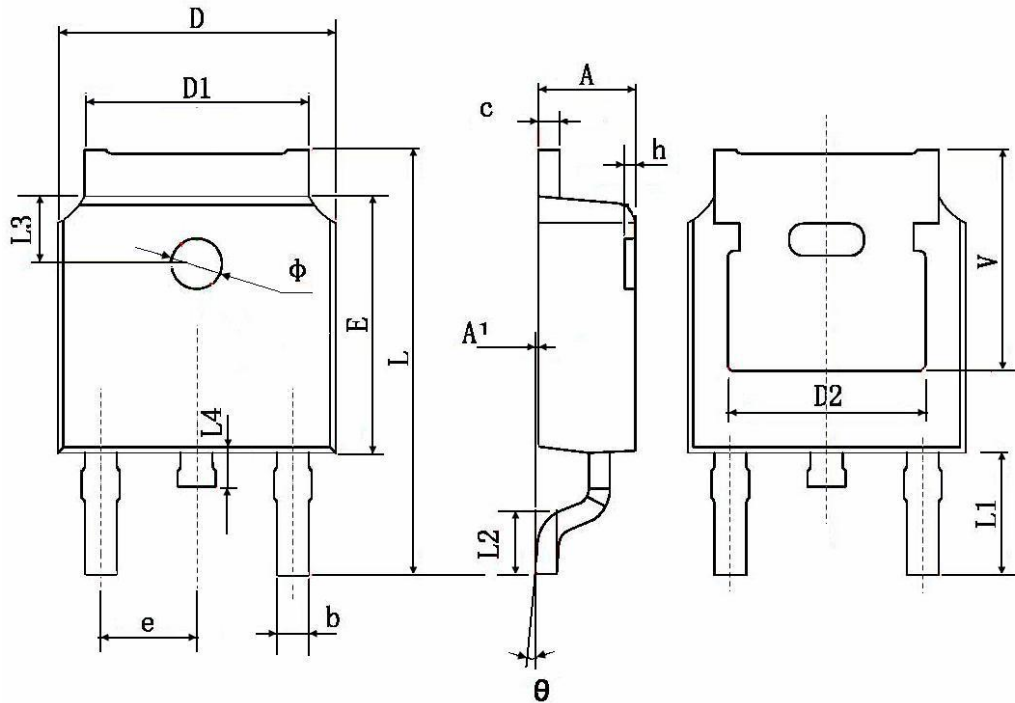


Unclamped Inductive Switching Test Circuit & Waveforms





TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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